

Features:

- 50 kV electrical isolation
- Choice of phototransistor or photodarlington output
- High speed 5 Mbit/sec (NRZ) OPI155 only
- Hermetically sealed LED and photosensor
- Base contact lead for conventional transistor biasing



Description:

Each **OPI150** and **OPI153** is an optically coupled isolator that contains an infrared emitting diode and a NPN silicon phototransistor (OPI150) or photodarlington (OPI153), each sealed in an individual hermetically sealed package. The diode and phototransistor or diode and photodarlington are then optically coupled by means of a light pipe and mounted in a high dielectric plastic housing. These devices are designed for applications that require very high isolation between input and output.

The **OPI155** is a high-speed optical coupled isolator that contains a high speed monolithic photo-IC comprised of a photodiode and a DC amplifier that drives an open collector output Schottky transistor. It is optically coupled by means of an internal light pipe. The LED and sensor are both in separate hermetically sealed packages that are then mounted in a high dielectric plastic housing. This device is designed for applications that require high speed *and* high voltage isolation between the input and output.

Applications:

- Requiring high voltage isolation between input and output
- Electrical isolation in dirty environments
- Industrial equipment
- Medical equipment
- Office equipment





General Note

RoHS

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.



OPI150, OPI153, OPI155

Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Operating Temperature Range	-40° C to +85° C					
Storage Temperature Range	-40° C to +85° C					
Input-to-Output Isolation Voltage ⁽¹⁾⁽²⁾	±50 kVDC					
Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 seconds with soldering iron] $^{(3)}$	260° C					
Input Diode						
Continuous Forward Current	50 mA					
Reverse Voltage	3 V					
Power Dissipation ⁽⁴⁾	200 mW					
Output Phototransistor or Photodarlington (OPI150, OPI153)						
Collector-Base Voltage OPI150 OPI153	30 V 20 V					
Collector-Emitter Voltage OPI150 OPI153	30 V 15 V					
Emitter-Collector Voltage	5.0 V					
Power Dissipation ⁽⁵⁾	250 mW					
Output Photosensor (OPI155)						
Supply Voltage	-0.5 to 7 V					
Output Voltage	-0.5 to 18 V					
Output Current	25 mA					
Open-Collector Power Dissipation	40 mW					
Power Dissipation ⁽⁵⁾	250 mW					

Notes:

(1) For OPI150 and OPI153, measured with input leads and output leads shorted.

(2) For OPI155, measured with input and output leads shorted and relative humidity of less than 50%.

(3) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.

(4) Derate linearly 3.33 mW/° C above 25° C.

(5) Derate linearly 4.17 mW/° C above 25° C.

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Electrical Specifications

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS		
Input Diode (For OPI150 & OPI153, see OP236 for additional information - for reference only. For OPI155, see OP235W for additional information - for reference only.)								
V _F	Forward Voltage OPI150, OPI153 OPI155	-	1.3 1.2	1.6 1.6	V	I _F = 50 mA I _F = 10 mA		
I _R	Reverse Current	-	0.1	100	μA	$V_R = 3 V$		
Output Phototransistor or Photodarlington (For OPI150, see OP805SL for additional information, for OPI153, see OP830SL for additional information- for reference only.)								
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage OPI150 OPI153	30 15	-	-	V	I _c = 1 mA		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage OPI150, OPI153	5	-	-	V	Ι _F = 100 μΑ		
V _{(BR)CBO}	Collector-Base Breakdown Voltage OPI150 OPI153	30 20	-	-	V	I _C = 100 μA		
I _{CEO}	Collector-Emitter Dark Current OPI150 OPI153	-	-	100 500	nA	V _{CE} = 10 V		
I _{CBO}	Collector-Base Dark Current OPI150	-	-	-	nA	V _{CB} = 10 V		
Coupled (OPI150, OPI153)								
I _{C/} I _F	DC Current Transfer Ratio OPI150 OPI153	10 25	-	-	%	I _F = 10 mA, V _{CE} = 5 V I _F = 20 mA, V _{CE} = 5 V		
I _{CB(ON)}	Ib0State Photodiode Current OPI150	10	-	-	μΑ	I _F = 20 mA, V _{CB} = 5 V		
V _{CE(SAT)}	Saturation Voltage OPI150 OPI153	-	-	0.5 1.2	V	I _F = 16 mA, I _C = 1 mA I _F = 30 mA, I _C = 2 mA		

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OPI150, OPI153, OPI155

Electrical Specifications

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS		
Output Photosensor (OPI155)								
I _{он}	High Level Output Current OPI155	-	-	250	μA	V_{O} = 18 V, I _F = 0, V _{CC} = Open		
I _{ссн}	High Level Supply Current OPI155	-	-	6.5	mA	V_{cc} = 5.25 V, I _F = 0, V _o = Open		
I _{CCL}	Low Level Supply Current OPI155	-	-	10	mA	$V_{CC} = 5.25 \text{ V}, \text{ I}_{\text{F}} = 10 \text{ mA}, \text{ V}_{\text{O}} = 0$		
V _{OL}	Low Level Output Voltage OPI155	-	-	0.5	V	$V_{CC} = 5.25 \text{ V}, \text{ I}_{\text{F}} = 10 \text{ mA}, \text{ I}_{0} = 8 \text{ mA}$		
Switching Characteristics (OPI155)								
T _{PHL}	Propagation Delay, High to Low	-	120	150	ns	V_{CC} = 5 V, I_{F} = 10 mA, R_{L} = 360 Ω		
T _{PLH}	Propagation Delay, Low to High	-	70	100				

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